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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/617,667 07/14/2003		Jun Sumino	67161-068	4737		
75	90 07/12/2004	EXAMINER				
McDermott, Will & Emery 600 13th Street, N.W. Washington, DC 20005-3096			PRENTY,	PRENTY, MARK V		
			ART UNIT	PAPER NUMBER		
washington, 2	20000 2000	2822				
			DATE MAILED: 07/12/2004			

Please find below and/or attached an Office communication concerning this application or proceeding.

					NVV		
		Application	No.	Applicant(s)	······································		
·		10/617,667		SUMINO ET AL.			
	Office Action Summary	Examiner		Art Unit			
		MARK V PF	RENTY	2822			
Period f	The MAILING DATE of this communication a or Reply	app ars on the o	cover she t with the	correspondence addr	ess		
THE - Ext afte - If th - If N - Fail	HORTENED STATUTORY PERIOD FOR REF MAILING DATE OF THIS COMMUNICATION ensions of time may be available under the provisions of 37 CFR or SIX (6) MONTHS from the mailing date of this communication. The period for reply specified above is less than thirty (30) days, a recommendation of the period for reply is specified above, the maximum statutory period to the period for reply within the set or extended period for reply will, by static reply received by the Office later than three months after the mained patent term adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no even reply within the statute od will apply and will tute, cause the applic	t, however, may a reply be to bry minimum of thirty (30) da expire SIX (6) MONTHS fror ation to become ABANDON	mely filed ys will be considered timely. n the mailing date of this com ED (35 U.S.C. § 133).	munication.		
Status							
1)🖂	Responsive to communication(s) filed on 14	July 2003.					
2a) <u></u>							
3)[	Since this application is in condition for allow	vance except fo	or formal matters, pr	rosecution as to the n	nerits is		
	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposi	tion of Claims						
4)⊠	Claim(s) <u>1-9</u> is/are pending in the application.  4a) Of the above claim(s) is/are withdrawn from consideration.						
5)□	☐ Claim(s) is/are allowed.						
6)⊠	☑ Claim(s) <u>1,7 and 8</u> is/are rejected.						
·	Claim(s) <u>2-6 and 9</u> is/are objected to.						
8)∐	Claim(s) are subject to restriction and	d/or election red	quirement.				
Applica	tion Papers						
9)[	The specification is objected to by the Exami	iner.					
10)⊠	oxtimes The drawing(s) filed on <u>14 July 2003</u> is/are: a) $oxtimes$ accepted or b) $oxtimes$ objected to by the Examiner.						
	Applicant may not request that any objection to the		•	• • • • • • • • • • • • • • • • • • • •			
44)	Replacement drawing sheet(s) including the corre	·		-			
11)	The oath or declaration is objected to by the	Examiner. Not	e the attached Offic	e Action or form PTC	)-152.		
Priority	under 35 U.S.C. § 119						
	Acknowledgment is made of a claim for foreign	ents have been ents have been riority documer	received. received in Applica its have been receiv	tion No	tage		
*	See the attached detailed Office action for a li	•		ed.			
Attachme	nt(s)						
	ce of References Cited (PTO-892)	4	Interview Summar				
	ce of Draftsperson's Patent Drawing Review (PTO-948) rmation Disclosure Statement(s) (PTO-1449 or PTO/SB/0	(80	Paper No(s)/Mail [ 5) Notice of Informal	Pate Patent Application (PTO-1	52)		
	er No(s)/Mail Date <i>July 14, 2003</i> .	,	6) Other:		•		

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This Office Action is in response to the papers filed on July 14, 2003.

Claims 1 and 7 are rejected under 35 U.S.C. 102(b) as being anticipated by Kanamori (United States Patent Application Publication 2002/0055217).

With respect to independent claim 1, Kanamori discloses a semiconductor device (see the entire reference, including the Fig. 4(b) disclosure, for example) comprising: a semiconductor substrate 1, having a main surface, in which first and second trenches 11 are formed in said main surface at a distance away from each other; first and second isolation insulating films 33 filling in said first and second trenches; a gate insulating film 2/30, formed on said main surface located between said first isolation insulating film and said second isolation insulating film, including silicon (oxide - note paragraphs [0057] and [0094), having an end portion 30 in a birds beak form which brings into contact with said first isolation insulating film and said second isolation insulating film, respectively; and a silicon film 3 formed on said gate insulating film, having a thickness exceeding 0 and being less than 50 nm (i.e., "approximately 50 to 150 nm" – see paragraph [0054]) in an intermediate portion between said first isolation insulating film and said second isolation insulating film, and being thinner than said thickness on said end portion.

Claim 1 is thus rejected under 35 U.S.C. 102(b) as being anticipated by Kanamori.

With respect to dependent claim 7, Kanamori's gate insulating film 2/30 has a first top surface, each of said first and second isolation insulating films 33 has a second top surface, and the distance from said main surface to said second top surface is greater than the distance from said main surface to said first top surface.

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Claim 7 is thus rejected under 35 U.S.C. 102(b) as being anticipated by Kanamori.

Claim 8 is rejected under 35 U.S.C. 103(a) as being unpatentable over Kanamori (United States Patent Application Publication 2002/0055217) together with Chen et al. (United States Patent 5,773,861 – hereafter Chen).

Claim 8 depends on independent claim 1, which was rejected above under 35 U.S.C. 102(b) as being anticipated by Kanamori. The above explanation of the rejection of independent claim 1 under 35 U.S.C. 102(b) as being anticipated by Kanamori is hereby incorporated by reference into this rejection of dependent claim 8 under 35 U.S.C. 103(a) as being unpatentable over Kanamori together with Chen.

The difference, therefore, between claim 8's semiconductor device and Kanamori's semiconductor device is claim 8's silicon film includes phosphorous.

Chen teaches that silicon floating gates are conventionally doped with arsenic or phosphorous to make them conductive (see column 5, lines 45-55, and column 6, lines 34-37).

It would have been obvious to one skilled in this art to dope Kanamori's silicon floating gate 3 with phosphorous, because Chen teaches that a silicon floating gate is conventionally doped with phosphorous to make it conductive.

Claim 8 is thus rejected under 35 U.S.C. 103(a) as being unpatentable over Kanamori together with Chen.

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Claims 2-6 and 9 are objected to as being dependent upon a rejected base

claim, but would be allowable over the prior art of record if rewritten in independent form

including all of the limitations of the base claim and any intervening claims.

The prior art of record does not disclose or suggest the allowable semiconductor

device taken as a whole, including the silicon film.

Shimizu (United States Patent 6,476,438), Lee et al. (United States Patent

6,515,329) and Satoh et al. (United States Patent 6,646,303) are relevant to this

application.

Registered practitioners can telephone the examiner at (571) 272-1843. Any

voicemail message left for the examiner must include the name and registration number

of the registered practitioner calling, and the Application/Control (Serial) Number.

Technology Center 2800's general telephone number is (571) 272-2800.

Mark V. Prenty

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Primary Examiner